

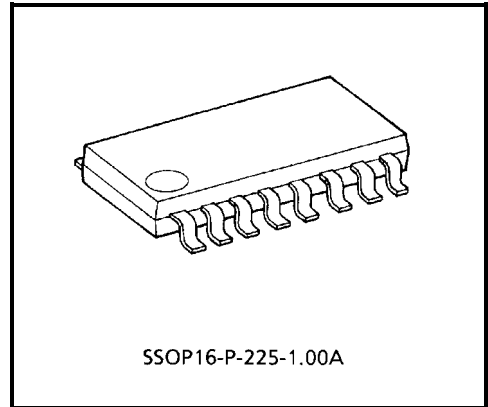
# TD62M2701F

## LOW SATURATION VOLTAGE H-BRIDGE DRIVER

TD62M2701F is multi-chip H-bridge driver IC incorporates 4 low saturation discrete transistors which equipped bias-resistor and fly-wheel diode. This IC is suitable for forward-reverse control on a battery use motor drive applications.

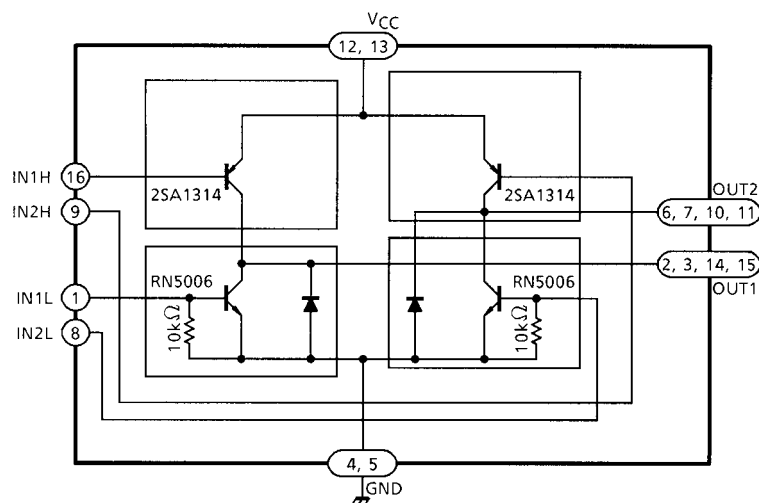
### FEATURES

- Suitable for high efficiency motor drive circuit
- Built-in fly-wheel diode (lower side)
- Built-in bias resistor (lower side) :  $R = 10\text{ k}\Omega$  (Typ.)
- SSOP 16 (1 mm pitch) package sealed
- Low saturation voltage
  - :  $V_{CE(sat)}(\text{upper} + \text{lower}) = 0.23\text{ V}$  (Typ.) :  $I_O = 1\text{ A}$
  - $= 0.45\text{ V}$  (Typ.) :  $I_O = 2\text{ A}$

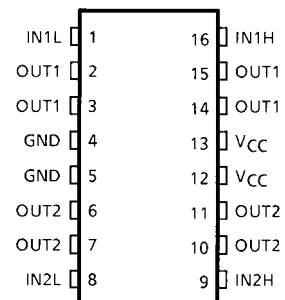


Weight: 0.14 g (Typ.)

### BLOCK DIAGRAM



### PIN CONNECTION (TOP VIEW)



## MAXIMUM RATINGS (Ta = 25°C)

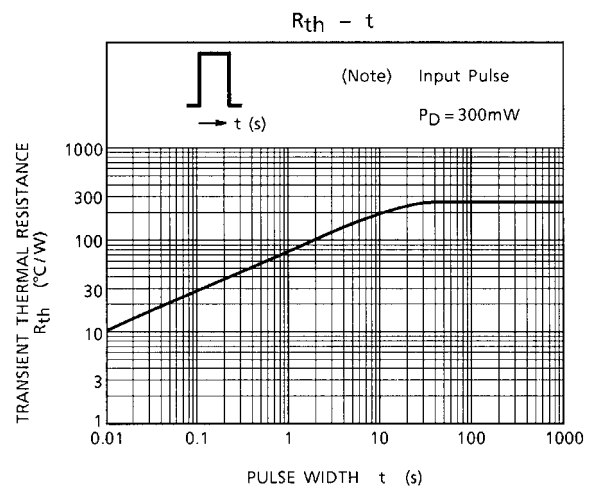
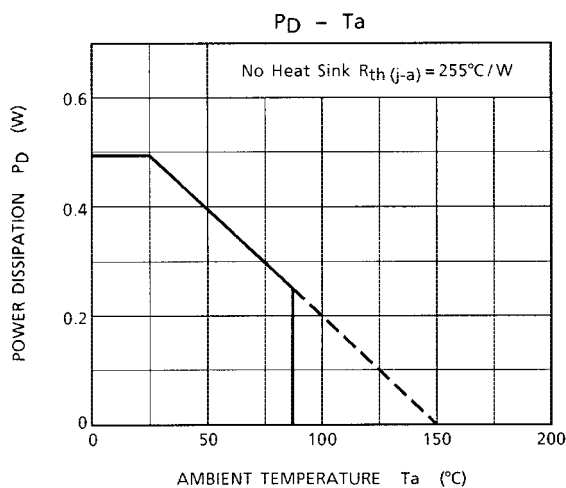
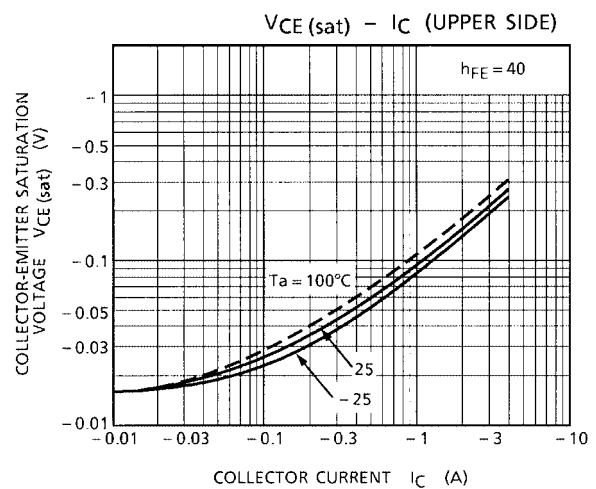
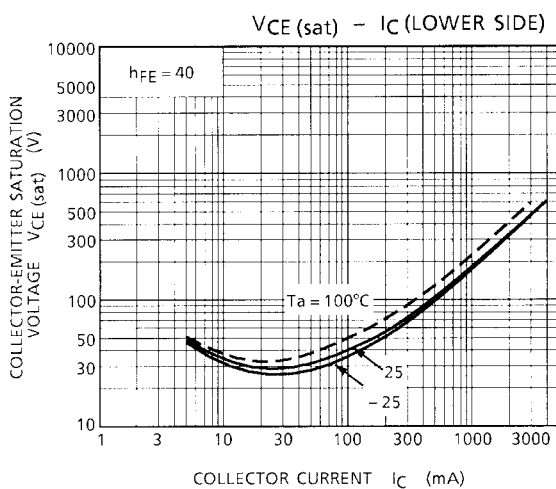
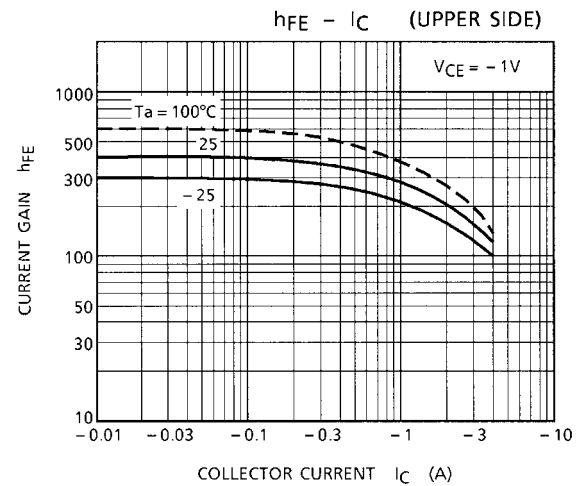
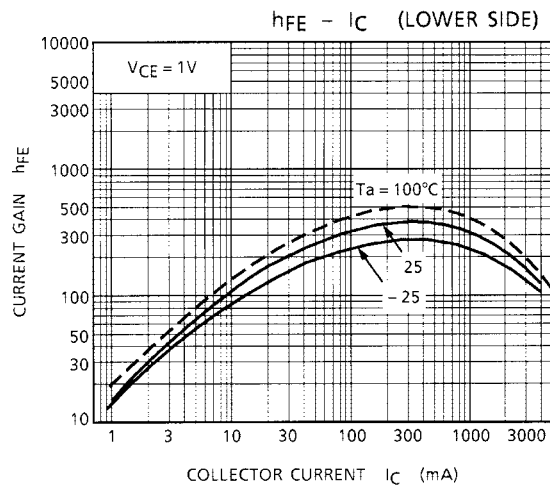
CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V <sub>CC</sub>	10	V
Collector-Base Voltage	V <sub>CBO</sub>	10	V
Collector-Emitter Voltage	V <sub>CER</sub>	10	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Output Current	I <sub>OUT</sub>	2	A
	I <sub>O</sub> (PEAK)	4 (Note 1)	
Base Current	I <sub>B</sub>	±0.4	A
	I <sub>B</sub> (PEAK)	±0.8 (Note 1)	
Diode Forward Current	I <sub>F</sub>	2 (Note 2)	A
Power Dissipation	P <sub>D</sub>	490	mW
Junction Temperature	T <sub>j</sub>	150	°C
Operating Temperature	T <sub>opr</sub>	-40~85	°C
Storage Temperature	T <sub>stg</sub>	-55~150	°C

Note 1: T = 10 ms Max. and maximum duty is less than 30%

Note 2: T = 10 ms single pulse

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CIR- CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Current Gain	Upper Side	$h_{FE(1)}$	—	$V_{CE} = -1\text{ V}, I_C = -0.5\text{ A}$	200	—	700	—
	Lower Side	$h_{FE(1)}$	—	$V_{CE} = 1\text{ V}, I_C = 0.5\text{ A}$	160	—	700	
		$h_{FE(2)}$	—	$V_{CE} = 1\text{ V}, I_C = 2.0\text{ A}$	60	130	—	
Output Saturation Voltage	Upper Side	$V_{CE(\text{sat})}$	—	$I_C = -1\text{A}, I_B = -25\text{ mA}$	—	-0.10	-0.22	V
				$I_C = -2\text{A}, I_B = -50\text{ mA}$	—	-0.20	-0.45	
	Lower Side			$I_C = 1\text{A}, I_B = 25\text{ mA}$	—	0.13	0.22	
				$I_C = 2\text{A}, I_B = 50\text{ mA}$	—	0.25	0.45	
	Summing Total			$I_C = 0.5\text{A}, I_B = 12.5\text{ mA}$	—	—	0.20	
				$I_C = 1\text{A}, I_B = 25\text{ mA}$	—	0.23	0.42	
				$I_C = 2\text{A}, I_B = 50\text{ mA}$	—	0.45	0.85	
Transition Frequency		$f_T$	—	$V_{CE} = 2\text{ V}, I_C = 0.5\text{ A}$	—	150	—	MHz
Output Leakage Current	Upper Side	$I_{OL}$	—	$V_{CC} = -10\text{ V}$	—	0	-5	$\mu\text{A}$
	Lower Side			$V_{CC} = 10\text{ V}$	—	0	5	
Diode Forward Voltage (Lower Side)		$V_F$	—	$I_F = 300\text{ mA}$	—	0.89	1.2	V
				$I_F = 450\text{ mA } 10\text{ ms}$	—	1.60	—	
Base-Emitter Resistance		$R_{BE}$	—	—	7	10	13	k $\Omega$
Base-Emitter Forward Voltage	Upper Side	$V_{BE(\text{PNP})}$	—	$V_{CE} = -1\text{ V}, I_C = -2\text{ A}$	—	-0.84	-1.5	V
	Lower Side	$V_{BE(\text{NPN})}$	—	$V_{CE} = 1\text{ V}, I_C = 2\text{ A}$	—	0.84	1.5	



## PRECAUTIONS FOR USING

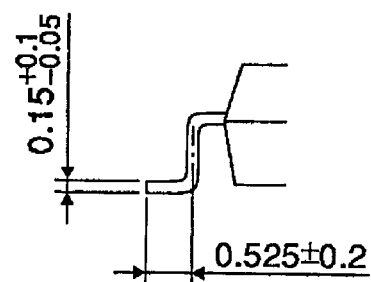
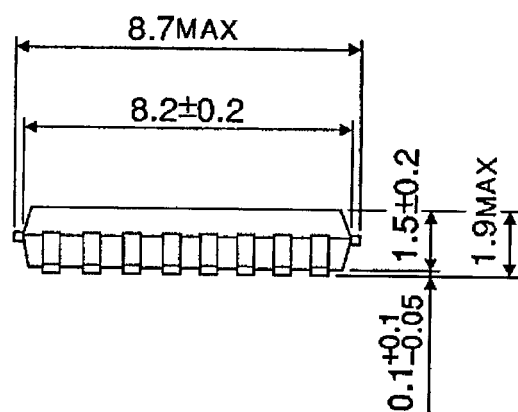
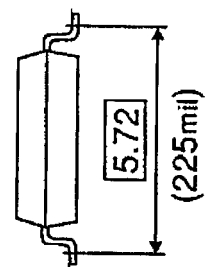
This IC does not integrate protection circuits such as overcurrent and overvoltage protectors.

Thus, if excess current or voltage is applied to the IC, the IC may be damaged. Please design the IC so that excess current or voltage will not be applied to the IC.

Utmost care is necessary in the design of the output line,  $V_{CC}$  and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

## SSOP16-P-225-1.00A

Unit: mm



Weight: 0.14 g (Typ.)

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